

## **MP3351** 60V, 2A Integrated Photo Flash Charger With IGBT Driver

The Future of Analog IC Technology

## DESCRIPTION

The MP3351 is a fast, highly efficient, precision high voltage photo-flash charger with integrated IGBT driver for xenon flash applications. The programmable peak current from 300mA to 2A. A 200m $\Omega$  internal power switch minimizes the conduction loss. 60V maximum output voltage lowers the transformer turns ratio and improves switching loss associated with the primary leakage inductance. External feedback provides 3% charge accuracy.

The MP3351 is available in a 16-pin 3mm x 3mm QFN package

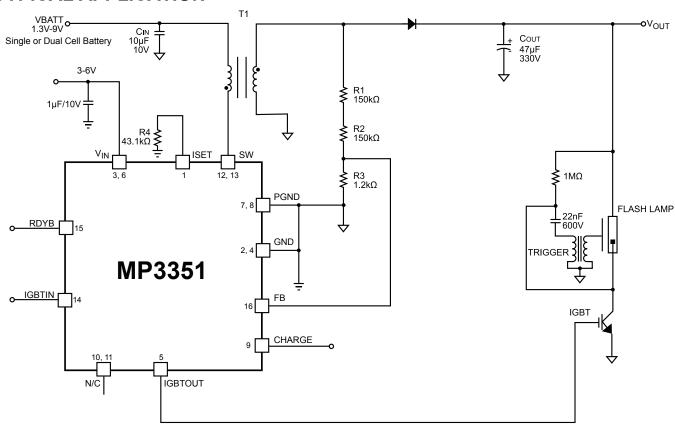
## FEATURES

- Integrated 60V, 200mΩ Power Switch
- Operates from a Single or Duel-Cell Li+ Battery
- 2A peak current w/resistor program
- 3% Charge Accuracy
- Integrated IGBT Driver

### **APPLICATIONS**

- Digital Still Cameras
- Optical Film Cameras
- Mobile Phones With Camera
- PDAs With Camera

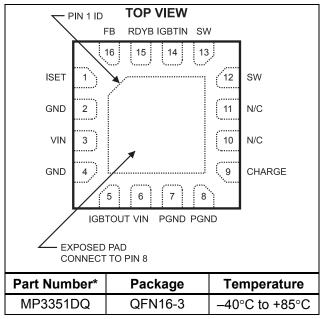
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### TYPICAL APPLICATION

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### PACKAGE REFERENCE

For Tape & Reel, add suffix –Z (eg. MP3351DQ–Z)
For RoHS compliant packaging, add suffix –LF (eg. MP3351DQ–LF–Z)

### ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>

| V <sub>IN</sub> to GND0.3V to 6V            |
|---|
| CHARGE, ISET, IGBTIN, RDYB to GND0.3V to 6V |
| FB to GND0.3V to 6V                         |
| SW to GND0.3V to 60V                        |
| Maximum Operating Frequency400kHz           |
| Operating Temperature Ranges40°C to +85°C   |
| Storage Temperature55°C to +150°C           |
| Junction Temperature+150°C                  |
| Lead Temperature (Solder)+260°C             |
| $T_{1}$                                     |

#### *Thermal Resistance* <sup>(2)</sup> *θ<sub>JA</sub> θ<sub>JC</sub>* QFN16 (3mm x 3mm)......50...... 12... °C/W

Notes:

1) Exceeding these ratings may damage the device.

2) Measured on approximately 1" square of 1 oz copper.

## ELECTRICAL CHARACTERISTICS

(V<sub>IN</sub>=V (CHARGE)=3.3V, T<sub>A</sub> = +25°C, unless otherwise noted.)

| Parameter                              | Conditions   | Min   | Тур  | Max   | Unit |
|--|--|-------|------|-------|------|
| Photoflash Capacitor Charger           |  |       |      |       |      |
| V <sub>IN</sub> Voltage Range          |  | 3     |      | 6     | V    |
| V <sub>IN</sub> UVLO                   | Rising edge, hysteresis = 200mV                              | 2.7   | 2.8  | 2.9   | V    |
| V <sub>IN</sub> Quiescent Current      | V(CHARGE)=High, V(SW) = 0, free<br>run by T <sub>ONMAX</sub> |       | 2.5  | 5     | mA   |
| V <sub>IN</sub> Quiescent Current      | V(CHARGE)=High, V(FB) = 1.3V                                 |       | 50   |       | μA   |
| Shutdown Current from $V_{IN}$         | V(CHARGE)=Low, V <sub>IN</sub> =3.3V                         |       |      | 1     | μA   |
| V <sub>SW</sub> Leakage Current        | $V_{IN}$ =3.3V, $V_{SW}$ =60V, in Shutdown                   |       |      | 2     | μA   |
| SW ON resistance between SW and GND    | Switch turn-on   |       | 0.2  |       | Ω    |
| Charge Input High Voltage              |  | 2.4   |      |       | V    |
| Charge Input Low Voltage               |  |       |      | 0.6   | V    |
| Pull-down resistance of<br>CHARGE pin  | V(CHARGE)=3.3V   |       | 100  |       | kΩ   |
| I <sub>PEAK1</sub>                     | R <sub>SET</sub> =43.1kΩ                                     | 1.08  | 1.20 | 1.32  | А    |
| I <sub>PEAK2</sub>                     | R <sub>SET</sub> =100kΩ                                      | 0.3   | 0.5  | 0.7   | А    |
| Charge completion detect voltage at FB |  | 1.176 | 1.20 | 1.224 | V    |
| FB input bias current I(FB)            |  | -0.2  |      | 0.2   | μA   |
| DCM Comparator threshold               | With 1.2K $\Omega$ (1%) connected to FB                      | 15    | 25   | 35    | mV   |

## ELECTRICAL CHARACTERISTICS (continued)

| Parameter                       | Conditions   | Min | Тур  | Мах | Unit |
|---------------------------------|--|-----|------|-----|------|
| RDYB Leakage Current            | V(RDYB)=3.3V   |     |      | 1   | μA   |
| RDYB Output Low Voltage         | I <sub>SINK</sub> = 2mA  |     | 0.2  |     | V    |
| MAX T <sub>ON</sub>             | Maximum T <sub>ON</sub> time   | 50  | 80   | 120 | μs   |
| Thermal Shutdown                | Rising edge, Hysteresis = 15°C   |     | 150  |     | °C   |
| IGBT Driver                     |  | ·   |      |     |      |
| IGBTOUT pull-up ON resistance   |  |     | 4    |     | Ω    |
| IGBTOUT pull-down ON resistance |  |     | 4    |     | Ω    |
| IGBTIN Input High Voltage       |  | 2.4 |      |     | V    |
| IGBTIN Input Low Voltage        |  |     |      | 0.6 | V    |
| Propagation delay               | IGBTIN rising/falling edge to<br>IGBTOUT rising/falling edge,<br>C <sub>GATE</sub> =6500pF |     | 45   |     | ns   |
| IGBTOUT rise time               | C <sub>GATE</sub> =6500pF  |     | 60   |     | ns   |
| IGBTOUT fall time               | C <sub>GATE</sub> =6500pF  |     | 70   |     | ns   |
| Pull down resistance of IGBTIN  |  |     | 100K |     | Ω    |

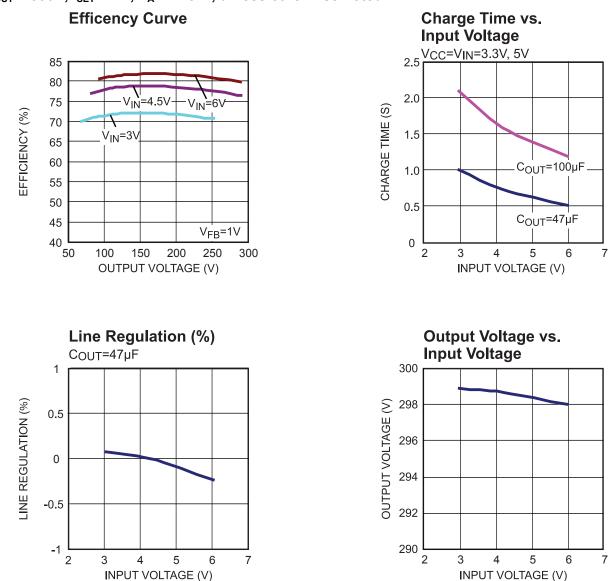
### (V<sub>IN</sub>=V (CHARGE)=3.3V, T<sub>A</sub> = +25°C, unless otherwise noted.)

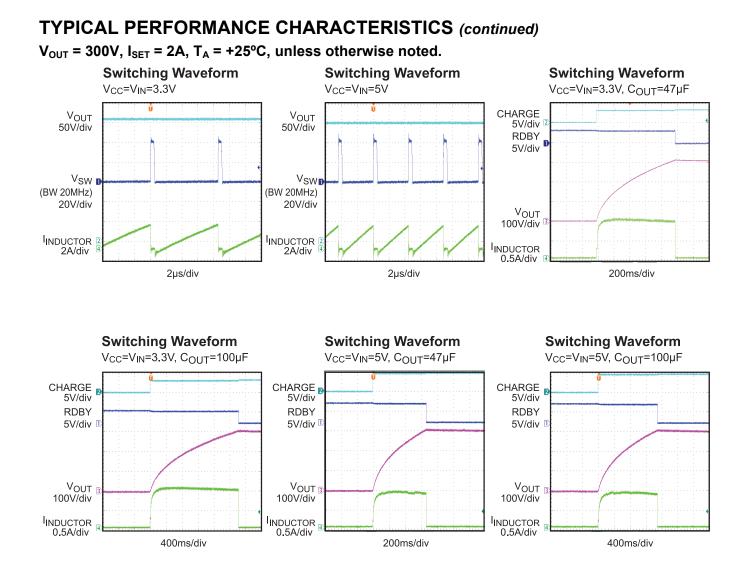
### **PIN FUNCTIONS**

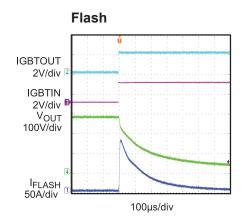
| Pin#   | Name                 | Description   |  |  |
|--------|----------------------|---|--|--|
| 1      | ISET                 | Peak Current Set Input. The peak current is $5 \times 10^4$ the current flow out of this pin.   |  |  |
| 2, 4   | GND                  | Analog Ground. Tie it directly to local ground plane.   |  |  |
| 3, 6   | VIN                  | Input Supply Pin. Connect it to system supply voltage. Bypass VIN to GND with 0.1uF or greater ceramic capacitor.   |  |  |
| 5      | IGBTOUT              | Output Drive for IGBT Gate. Connect this pin to the gate of the IGBT.   |  |  |
| 7, 8   | PGND,<br>Exposed Pad | Power Ground. Ground connection for the power switch. Connect Exposed Pad to PGND.  |  |  |
| 9      | CHARGE               | Charge Enable Pin. A low to high transition on this pin puts the part into power delivery mode. Once the target voltage is reached, the part will stop charging the output. Toggle this pin will start charging again. Bring this pin low will terminate the power delivery and put the part in shutdown. |  |  |
| 12, 13 | SW                   | Switch Pin. This is the drain of the internal power switch.   |  |  |
| 14     | IGBTIN               | Logic Input Pin for IGBT Drive.   |  |  |
| 15     | RDYB                 | Open-Drain Power-Ready Output. RDYB becomes low when the output voltage is reached.   |  |  |
| 16     | FB                   | Feedback Pin. Its trip voltage is 1.2V.   |  |  |

## **TYPICAL PERFORMANCE CHARACTERISTICS**

 $V_{OUT}$  = 300V,  $I_{SET}$  = 2A,  $T_A$  = +25°C, unless otherwise noted.









## **BLOCK DIAGRAM**

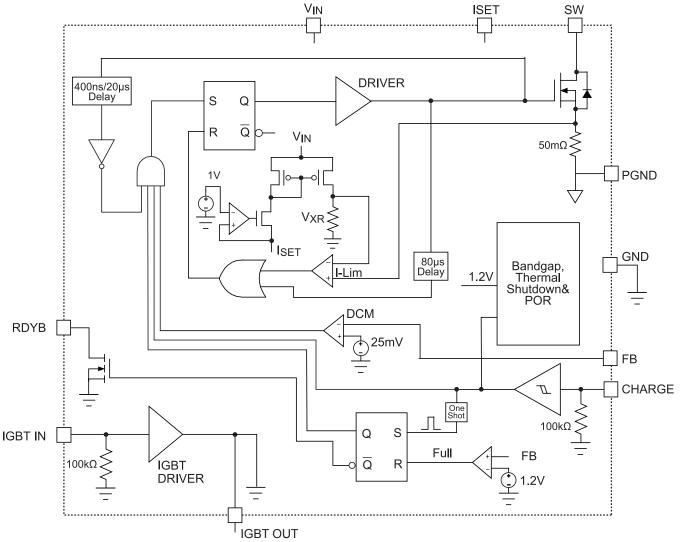


Figure 1—Functional Block Diagram

### **APPLICATION INFORMATION**

MP3351 controlled flyback charger operates in critical conduction mode with peak current set by ISET pin. Output voltage is divided down through R1, R2 and R3 from the positive terminal of the transformer secondary and compares with 1.20V at FB pin. The low to high transition of CHARGE pin will enable the flyback converter to switch.

A minimum  $T_{OFF}$  of 20µS provides a minimum OFF time at the beginning of charging when DCM comparator always trips because V<sub>OUT</sub> is still near zero, Min T<sub>OFF</sub> will be reduced to 400nS after  $V_0$ >16V. Charger may enter DCM mode when charge is close to full and actual OFF time is less than minimum T<sub>OFF</sub>. Circuit will stop switching and RDYB will be pulled low once the flash capacitor is charged to 300V, a value set by R1, R2 and R3. When the part is ready the internal dissipation is reduced to just the circuits for IGBT driver. Toggle CHARGE pin will start charge again. Bringing CHARGE pin low terminates the power delivery and put the part in shutdown. A maximum  $T_{ON}$  timer prevents pulling current from starved power source. If the ON time exceeds maximum  $T_{ON}$ , the switch is forced OFF regardless of IPEAK detection. Integrated IGBT driver uses V<sub>IN</sub> as its power supply.

### **DCM Comparator**

DCM boundary is reached when V(FB) drops to zero. The DCM comparator compares V(FB) and a fixed offset voltage of 25mV to account for the comparator delay.

### **Charge Speed**

The output capacitor charging speed is determined by:

$$T_{\text{CHARGE}} \propto \frac{I_{\text{LIM}}}{\frac{1}{V_{\text{IN}}} + \frac{N}{V_{\text{OUT}}}}$$

#### Setting Peak Charge Current

MP3351's peak charge current ( $I_{SET}$ ) can be set by an external resistor,  $R_{SET}$  from the ISET pin to ground. The value of  $R_{SET}$  can be calculated from:

$$\mathsf{R}_{\mathsf{SET}}(\mathsf{K}\Omega) = \frac{50}{\mathsf{I}_{\mathsf{SET}}(\mathsf{A})}$$

For example, for 2A peak charge current, RSET is  $24.9k\Omega$ .

#### **Primary Inductance**

The primary inductance is calculated based on the minimum off time period:

$$L_{\text{PRIMARY}} \geq \frac{V_{\text{OUT}} T_{\text{MIN,OFF}}}{N I_{\text{PEAK}}}$$

 $V_{OUT}$ : output voltage about 300V  $T_{MIN, OFF}$ : Minimum off time 400nsec.  $I_{PEAK}$ : primary peak current

#### **Turns Ratio**

The minimum turns ratio of the flyback transformer is obtained as:

$$N \ge \frac{V_{OUT}}{V_{DS} - V_{IN}}$$

 $V_{\text{DS}}$ : FET drain-source voltage  $V_{\text{IN}}$ : Input voltage 3~5V

### **Setting Output Voltage**

The output voltage is set by selecting the resistive voltage divider ratio. If we use 1.2k For the low side resistor (R3) of the voltage divider, we can determine the high side resistor (R1, R2) by the equation:

$$R1 = R2 = \frac{1}{2} \frac{V_{OUT} - V_{FB}}{V_{FB}} R3$$

Typical values are R1=R2=150k $\Omega$  and R3=1.2k $\Omega$ .

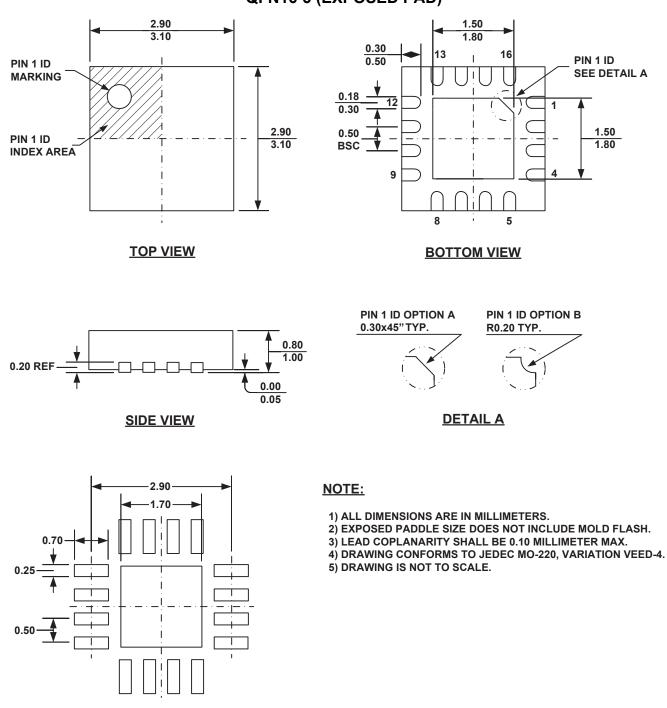
### **Output Diode Selection**

The reverse voltage of the output diode is determined by:

$$V^{}_{\rm D} = V^{}_{\rm OUT} + N V^{}_{\rm IN}$$



### **PACKAGE INFORMATION**



QFN16-3 (EXPOSED PAD)

#### **RECOMMENDED LAND PATTERN**

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